

Description

The VSM2333Y uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

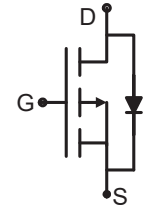
- $V_{DS} = -12V, I_D = -6A$
 $R_{DS(ON)} < 45m\Omega(max) @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 30m\Omega(max) @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



SOT-23-3



Schematic Diagram

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM2333Y-S2	VSM2333Y	SOT-23-3	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current -Continuous	I_D	-6	A
Drain Current -Pulsed ^(Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	1.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	69	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-12	-	-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.65	-1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-6A	-	19	30	mΩ
		V _{GS} =-2.5V, I _D =-5A	-	26	45	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-6A		17	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-6V, V _{GS} =0V, F=1.0MHz	-	1100	-	PF
Output Capacitance	C _{oss}		-	390	-	PF
Reverse Transfer Capacitance	C _{rss}		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-6V, I _D =-1A , R _L =6Ω, V _{GEN} =-4.5V, R _g =6Ω	-	25	-	nS
Turn-on Rise Time	t _r		-	45	-	nS
Turn-Off Delay Time	t _{d(off)}		-	72	-	nS
Turn-Off Fall Time	t _f		-	60	-	nS
Total Gate Charge	Q _g	V _{DS} =-6V, I _D =-6A, V _{GS} =-4.5V	-	11.5	-	nC
Gate-Source Charge	Q _{gs}		-	1.5	-	nC
Gate-Drain Charge	Q _{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-1.0A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-6	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

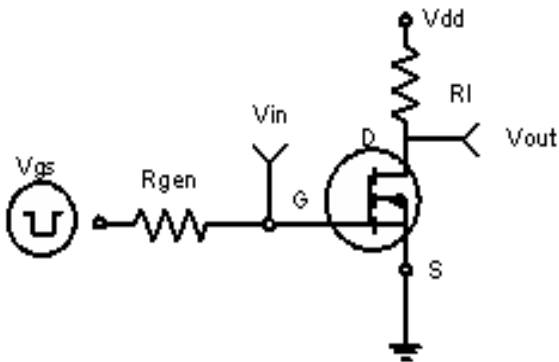


Figure 1: Switching Test Circuit

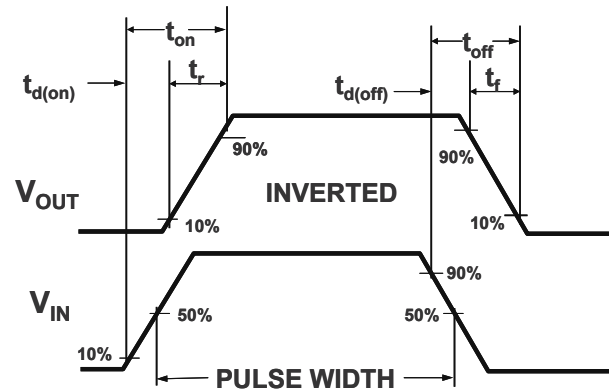


Figure 2: Switching Waveforms

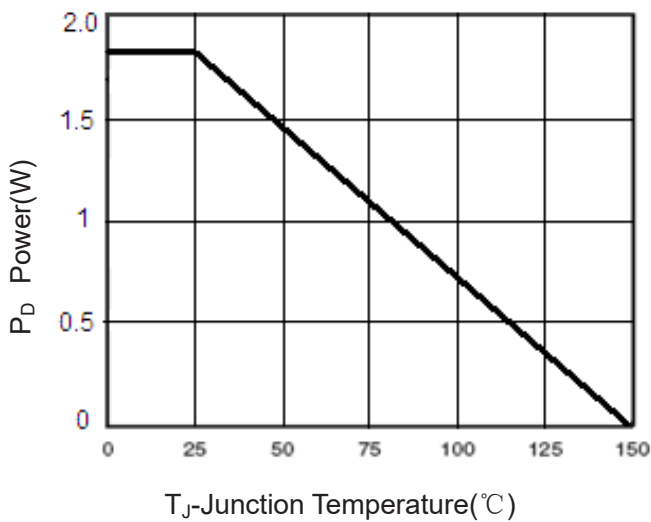


Figure 3 Power Dissipation

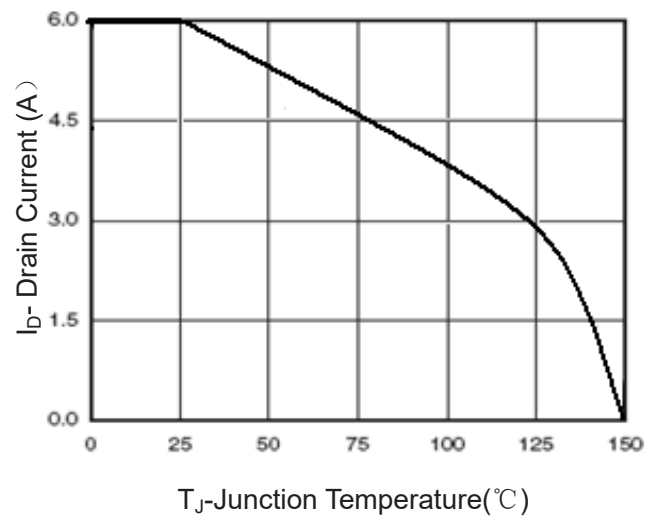


Figure 4 Drain Current

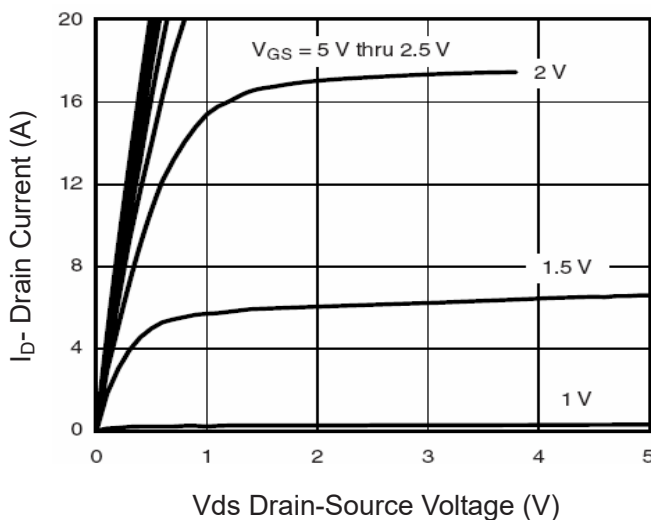


Figure 5 Output Characteristics

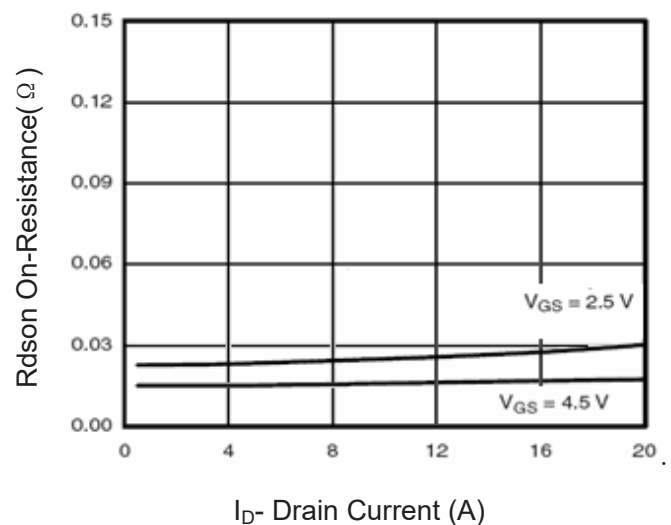
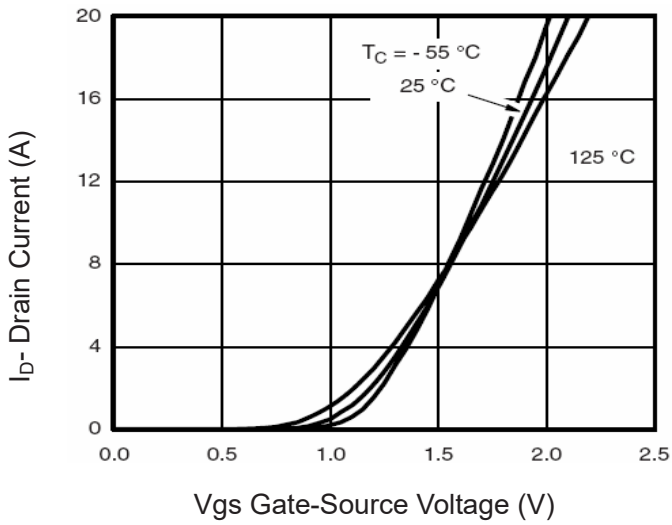
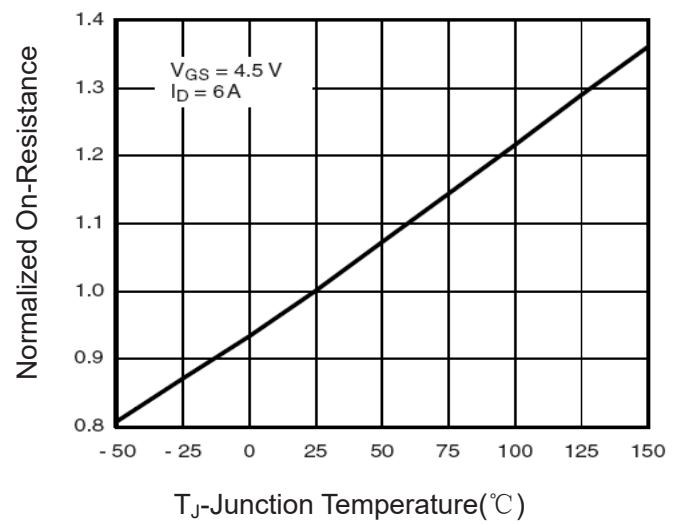
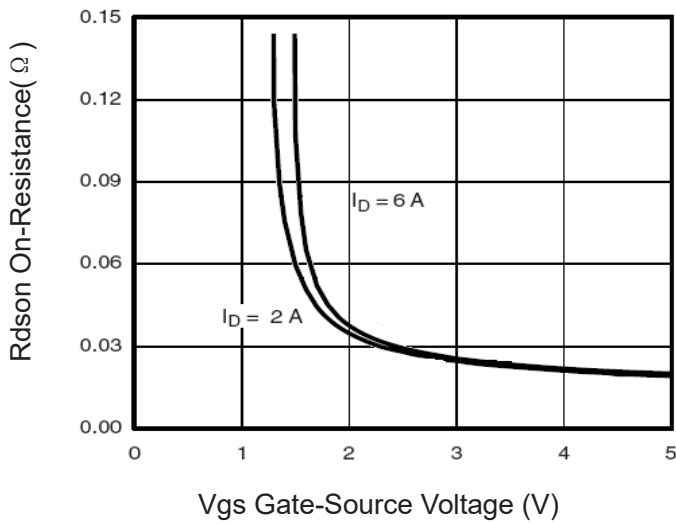
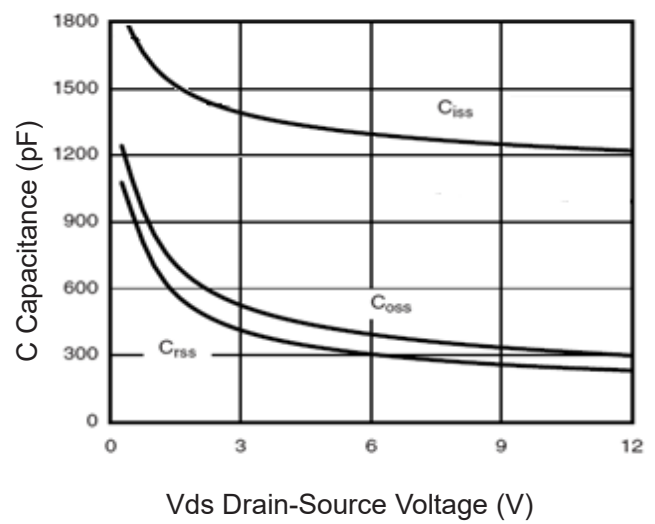
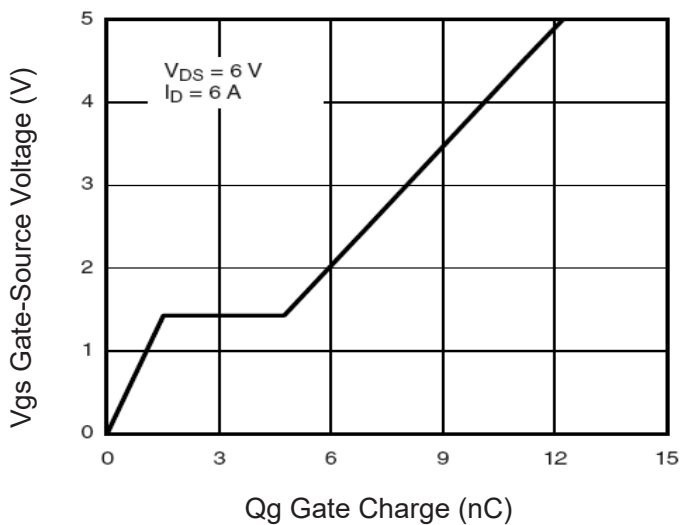
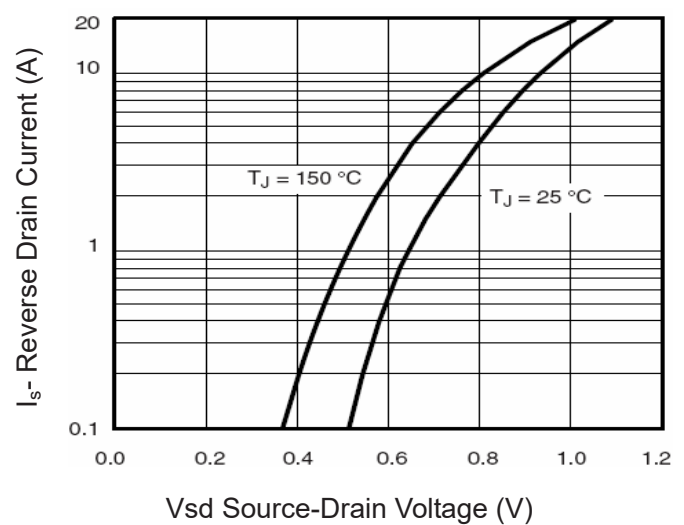
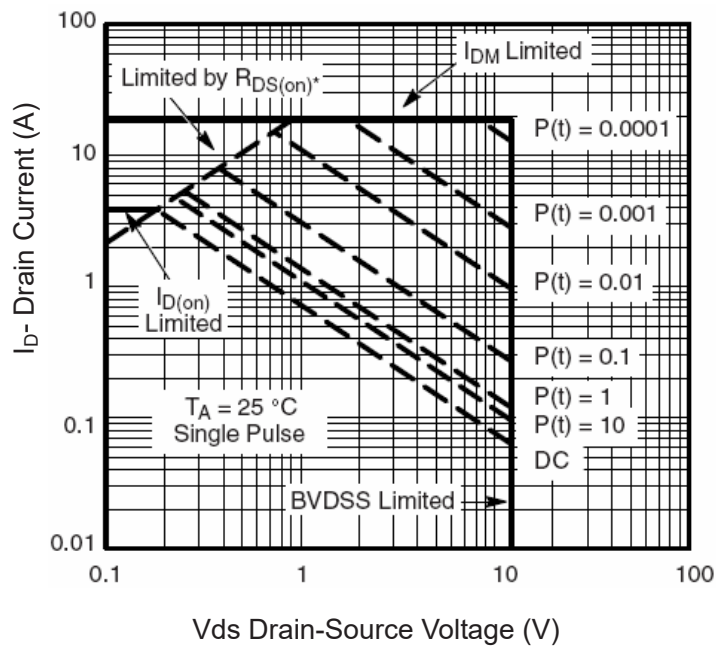
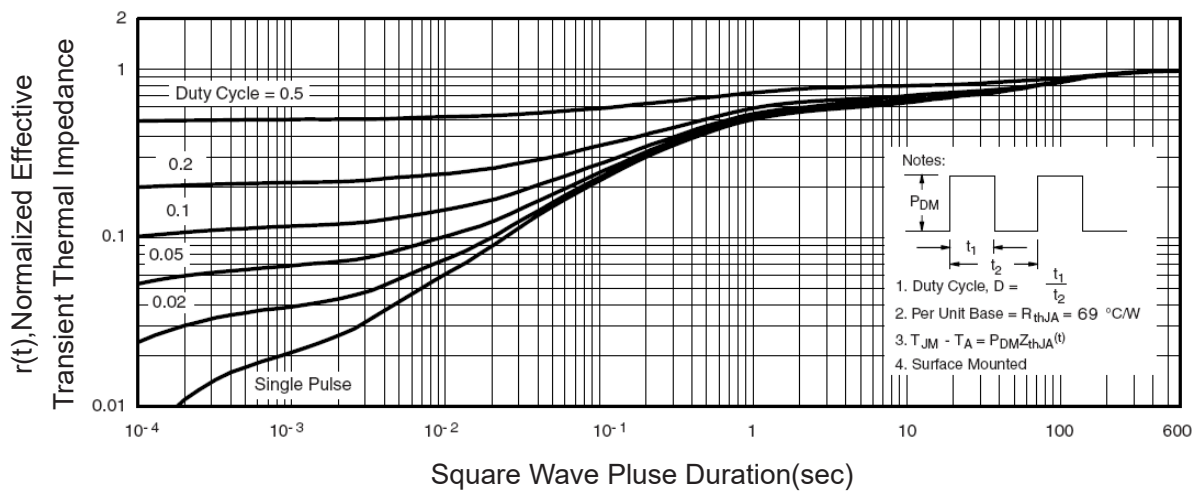


Figure 6 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 8 Drain-Source On-Resistance

Figure 9 Rdson vs Vgs

Figure 10 Capacitance vs Vds

Figure 11 Gate Charge

Figure 12 Source- Drain Diode Forward


Figure 13 Safe Operation Area

Figure 14 Normalized Maximum Transient Thermal Impedance